

ABSTRACT OF THE DISCLOSURE

In a semiconductor integrated circuit device, an integrated circuit portion is provided on a surface of a P-type silicon substrate and in a multilayer interconnection layer. The semiconductor integrated circuit device also includes a temperature sensor portion. At the higher level than the multilayer interconnection layer, a sheet member formed of vanadium oxide is provided. The sheet member and a resistor are connected in series between a ground potential wiring and a power-supply potential wiring, and an output terminal is connected to a connection point between the sheet member and the resistor.